Perspective on EIC activities in India

Ganesh Tambave On behalf of EIC-India Group 16.03.2023 EIC-Asia Workshop, RIKEN, Japan

Indian groups participation in HI collision experiments

Active participation in QCD physics experiments: STAR@RICH, ALICE@LHC, CBM@FAIR and CMS@LHC

Institution	Experiment/Facility	Approx number of persons
Univ. of Jammu	STAR@RHIC, ALICE@LHC, CBM@FAIR	10
Univ. of Panjab	STAR@RHIC, ALICE@LHC, CBM@FAIR	10
Univ. of Rajasthan	STAR@RHIC, ALICE@LHC	2
Inst. of Phy. BBSR	STAR@RHIC, ALICE@LHC, CBM@FAIR	4
NISER, BBSR	STAR@RHIC, ALICE@LHC, CBM@FAIR	12
VECC, Kolkata	STAR@RHIC, ALICE@LHC, CBM@FAIR	15
IIT, Bombay	STAR@RHIC, ALICE@LHC	8
SINP, Kolkata	ALICE@LHC	8
Bose Inst. Kolkata	ALICE@LHC, CBM@FAIR	8
IIT, Indore	ALICE@LHC CBM@FAIR	10
BHU, Varanasi	PHENIX@RHIC, CBM@FAIR	3
AMU, Aligrah	ALICE@LHC, CBM@FAIR	6
BARC, Mumbai	PHENIX@RHIC, CMS@LHC, ALICE@LHC	10
Gauhati Univ.	ALICE@LHC, CBM@FAIR	3
Univ. Calcutta	CBM@FAIR	4
IISER, Tirupati	STAR@RHIC	3
IISER, Berhampur	STAR@RHIC	2
IIT, Patna	STAR@RHIC	2
IIT Madras	CMS@LHC	4
19 Institutes	RHIC, LHC, FAIR	124

Indian groups contribution in HI collision experiments

Institution	Physics, Detector, Experiment (selected list only)		
Univ. of Jammu	Heavy Flavour Physics, PMD, DCS, Trigger, GRID computing, STAR HFT, ALICE-FOCAL, EIC		
Univ. of Panjab	Fluctuation and correlations, photon multiplicity, nuclei production, BES-II-RHIC, CBM, EIC		
Univ. of Rajasthan	Anisotropic flow, photon multiplicity		
Inst. of Phy. BBSR	Light hadron spectra, PMD, GEM, CBM, EIC		
NISER, BBSR	Spectra, fluctuations, azimuthal anisotropy, RHIC-BES, CBM-RPC, GEM, ALICE-FOCAL, EIC		
VECC, Kolkata	PMD, MUCH, fluctuations, correlations, Jet physics, ALICE-TPC, ALICE-FOCAL, CBM- MUCH, CRU, Electronics, Grid Computing	Experimental participation to achie	ve science goals
IIT, Bombay	Resonance, fluctuations, correlations, simulations, ALICE-FOCAL, EIC	Experiments/Facility Nature of participation and time I	Nature of participation and time line
SINP, Kolkata	Muon Spectrometer ALICE, High Level trigger, RAA, J/Psi, Upsilon		annon an an an Shara ann an Arthur a na an Ann a
Bose Inst. Kolkata	ALICE-TPC upgrade, photon multiplicity, ALICE-FOCAL, CBM	STAR Experiment Ream Energy Scan Phase - II -	Data taking and Physics Analysis
IIT, Indore	Photon Multiplicity, HBT, Freeze-out dynamics, CBM, EIC	Relativistic Heavy Ion Collider, BNL, USA 2014-2024	
BHU, Varanasi	Non-photonic electrons PHENIX@RHIC, CBM@FAIR, detector R&D EIC		
AMU, Aligrah	Heavy-quark Measurements, ALICE-Muon Detector, EIC		
BARC, Mumbai	Heavy-quark Measurements, Fluctuations and Correlations, jets, UPC, ALICE-FOCAL, GEM, RPC, Electronics	Compressed Baryonic Matter Experiment, FAIR facility, GSI, Germany	Detector for muon identification in CBM (RPC and GEM based)
IISER Tirupati and Berhampur IIT Patna	Physics Analysis at RHIC and EIC		Physics Analysis and Data Taking 2025 Onwards
PMD – Photo	n Multiplicity Detector, MUCH – Muon Chambers, TPC – Time Projection Chamber		
		LHC	Data taking, Physics Analysis

Active participation and significant contribution in software, data analysis and detector hardware related work

Detector and Electronics R&D – upgrades coping with higher luminosity and building radiation

hard detectors (silicon based).

2010 - 2030

Indian participation in EIC progress

- International Representative for Steering Committee: Asmita Mukherjee (IIT Bombay, India)
- Member of "Diversity and Inclusion Committee": Asmita Mukherjee (IIT Bombay, India)
- Member of "Elections and Nominating Committee": Bedangadas Mohanty (NISER, India)
- Member of "Integration Committee (ATHENA)": Bedangadas Mohanty (NISER, India)
- Member of "Bye laws and Charter Committee": Bedangadas Mohanty (NISER, India)
- EIC finds place in the Indian "Mega Science Vision (MSV) – 2035" document
- MSV 2035: A roadmap prepared by the Indian Nuclear Physics Community for long term future
- Recommendations for participation in Electron Ion Collider experiments to address the fundamental questions in nuclear physics and participate in detector development.

EIC physics contribution: Theory Colleagues

Initiated joint IITB – CFNS (theory) postdoc fellowship (50% funding from CFNS)

SciPost (Selected publication only)

SciPost Phys. Proc. 8, 017 (2022)

Sivers asymmetry in inelastic J/ψ leptoproduction at the EIC

S. Rajesh^{$1^{1^{1}}$}, U. D'Alesio^{1,2}, A. Mukherjee³, F. Murgia¹ and C. Pisano^{1,2}

 $\cos 2\phi_t$ azimuthal asymmetry in back-to-back J/ψ -jet production in $ep o eJ/\psi$ jet X at the EIC

Raj Kishore, Asmita Mukherjee, Amol Pawar, and Mariyah Siddiqah Phys. Rev. D **106**, 034009 – Published 10 August 2022

- International workshop on QCD with Electron-Ion Collider (QEIC), January 4-7, 2020, IIT Bombay, Mumbai
- The next workshop QEIC II will be held by IIT Delhi during Dec 18 20, 2022. Everyone here are invited to attend. <u>https://indico.cern.ch/event/1196913/</u>
- There is a possibility to receive seed funds from DAE and DST for next 3 years \rightarrow under discussion.

Indian long-range plan – Mega Science Vision 2035 – Nuclear Physics

QCD: Recommendations

The study of the emergent properties of QCD matter is one of the most compelling science problems in nuclear physics. It includes mapping the phase diagram of the QCD matter, measuring the properties of the QCD matter subjected to extreme conditions of temperature, pressure, baryon density, electromagnetic fields and angular momentum, finding out the partonic content of a nucleus and the fundamental mechanisms behind the properties of nucleons, such as its mass and spin.

We recommend continued participation in heavy-ion programs at LHC, RHIC and FAIR, the collision energies of which, only when taken together, allow to map the QCD phase diagram. While the CBM experiment, which is under construction at FAIR, should be the focus for the high-energy nuclear collisions in the near future, we also recommend participation in the upcoming Electron-Ion Collider experiments to address the fundamental questions in nuclear physics.



What are the phase structures of Quantum Chromodynamic (QCD) matter?







How do the strong interactions amongst quarks and gluons inside the nucleons result in confinement and collectively result in their properties such as mass and spin?



How does a nucleus look in terms of its partonic content? Does the gluon density saturate to gluonic matter of universal properties?

Indian Institutes interested in EIC





EIC India – Software contribution: Benchmarking



interface to read event record and pass the information to Geant4

Barrel Imaging Calorimeter (ATHENA): Optimization of Clustering Parameters (PU) dRICH (NISER): Photo-sensors optimization simulation with JUGLER



EIC India – Software contribution: Benchmarking EIC Simulation effort @ NISER



EIC-India collective research Proposal Detailed Project Report (DPR)

- All the interested Indian institute are working on the proposal together to our major funding agency in India, <u>plan to submit in coming four months</u>
- Hardware contribution/R&D is most important part of our proposal, the idea is to request money initially for R&D (2 - 3 years) and upon successful completion of R&D apply for mass production
- Funding agency strictly wants us to spend money locally (favours in-kind contribution), however there is some scope to purchase imported test equipment

Our Interest in ePIC detector system

Interests are based on what is possible to do in India

- 1. dRICH/hpDIRC (SiPM R&D) and
- 2. Zero Degree Calorimeter (p-type Si pad arrays and/or SiPM based calorimeter in ZDC)
- 3. Also some interest on Time of Flight (AC-LGAD R&D) R&D level
- 4. Interest expressed to contribute in DAQ and slow control



Regular attendance in PID and LGAD consortium weekly meetings, exploring possibilities for contribution

Proposed possible contributions

- If the proposal is successful, as the recommendation is to spend money locally; we plan to propose design, fabrication and testing of SiPM's and p-type pad arrays (also some R&D on AC-LGAD's) in India, the major cost would be to purchase of p-type epitaxial wafers and photomask
- The work would include TCAD device and process simulations, fabrication
- Qualification studies: Borrow/purchase readout ASIC and related DAQ
- Contribute in test beam experiments, data analysis etc.
- ePIC ZDC, RICH, ToF System commissioning and integration (in later stages)
- There are many other aspects where we could contribute later like, producing evaluation board PCB or ASIC carrier board PCB in India. The cost is very competitive to others. Any other work like production of cooling, mechanical structures is possible

SiPM, p-type Pad arrays, and AC-LGAD: Fabrication

- In discussion with design engineers from semiconductor Fabs in India
- Indian semiconductor fabs are experienced in silicon detector fabrication (SiPM, Pad arrays) as well as in readout ASIC (ROIC) chip fabrication
- They have capability of fabrication on 6" and 8" wafer and 180 nm process technology and also aim to acquire smaller process nodes (65 nm, 28 nm) in near future
- The preparation of the design specification for p-type pad array, SiPM, AC-LGAD is ongoing
- Seeking help from subject experts from collaboration for AC-LGAD fabrication (not done before)
- Possibility to fabricate readout ASICs in Indian fab
- In addition, our Fabs showed interested to cooperate in mass production

Available infrastructure and detector R&D: Si Fabs and their expertise

Semiconductor Lab (SCL), Mohali
Bharat Electronics Limited (BEL), Bangalore

Semiconductor Lab (SCL), Mohali - Capabilities

Process and fabrication

Design

Testing

Packaging and assembly

Reliability and quality assurance

https://www.scl.gov.in/

Future roadmap

Sr.	Technologies	2021-22	2022-23	2023-24	2024-25
No.					
1.	Establishment of GaN Technology for Detectors & High Power Devices				
2.	SiGe Bi-CMOS for High Speed Devices				
3.	Detectors: including Back side illumination in full spectrum range with compound semiconductors				
4.	Higher Technology Node (65nm/45nm/28nm)				

SCL background - detectors and ASICs

Photodiode Detectors for X-Ray Systems



Type A

- No of pixels: 16
- Pixel size: 3.2mm × 1.4mm
- Pixel pitch: 1.5 mm
- Chip size: 3.2mm × 24mm



- No of pixels: 1
- Pixel size: $3 \text{cm} \times 0.4 \text{cm}$
- Pixel pitch: 1.5 mm
- Chip size: 3.5cm x 0.5cm
- Dark current: < 0.5nA @1V
- Responsivity 0.3 A/W at wavelength of 540nm

BARC - Charged Particle Detectors

- Area: 450 sq. mm
- Reverse leakage current: <1nA @ 100V



BARC CPD (TOP VIEW)

VECC ASICs

Granular charged particle Multiplicity filter Detector Array (GMDA) and NFM (Neutron Flux Monitor)

	GMDA	NFM			
Detector Type	96 CSI(Tl) with PIN	Boron Trifluoride (BF3)			
Electronic Resolution	<1% of dynamic range	<1% of dynamic range			
Sensitivity	5mV/fC (CSA);	2mV/fC (CSA);			
	2.5mV/fC(shaper)	1mV/fC(shaper)			
Linearity	<1%	< 1%			
No of Channel	8	2			

Silicon Photo Multipliers (SD31xx-0Tx)

- Pixel architecture: N+/P well diode with Virtual Guard Ring
- Quenching type: Passive (~350kOhm) Quenching resistor:- Poly-silicon
- Isolation between pixels: Shallow trench isolation (0.38um deep)
- Break-down Voltage (VBD) : 22V
- Excess Bias: +2.5V
- Recovery Time: 100ns
- Leakage Current: <5nA/cm2 (at 20V & RT)
- Peak Wavelength: 510nm
- Gain: 5E5 to 1E6







SiPM Fabricated at SCL, Mohali



PRODUCT DESCRIPTION:

Silicon Photomultiplier is a novel, high gain, single photon sensitive sensor. It consists of parallel array of identical and independent avalanche photodiodes pixels, with each pixel diode connected to bias voltage supply through a series resistor (~few hundred kilo Ohms).

Device are available in:

- 1.5 x 1.5 sq. mm (pixel size 50um x 50um & 10um x 10um)
- 3 x 3 sq. mm (pixel size 50um x 50um & 10um x 10um)
- 3mm circular diameter

FEATURES:

- Breakdown Voltage (BV): 22 V
- Over-Bias voltage: 2V (max)
- Temperature coefficient of BV: 22mV/°C (Temperature Range :-243to 323 K)
- Total leakage current :<5nA/cm2 (at 20 V)
- Dark count rate: 350 to700kHz (3*3 sq mm) &

370 to 500 kHz (1.5*1.5 sq mm)

- Recovery time: 100ns
- Geometrical Fill factor: 70% for 50 um pixel size & 15% for 10 um pixel size SiPMs

Silicon Photo Multipliers (SD31xx-0Tx)

Pixel architecture: N+/P well diode with Virtual Guard Ring

Quenching type: Passive (~350kOhm) Quenching resistor:- Polysilicon

Isolation between pixels: Shallow trench isolation (0.38um deep)

Break-down Voltage (VBD): 22V

Excess Bias: +2.5V

Recovery Time: 100ns

Leakage Current: <5nA/cm2 (at 20V & RT) Peak Wavelength: 510nm

Gain: 5E5 to 1E6



SiPM Fabricated at SCL, Mohali



Size: 1.5 x 1.5 mm² Pixel size: 35 x 35 μ m² No of pixels: 1156











- Standard low voltage 180nm CMOS baseline process was adopted for realizing SPADs
- Some test samples are available

SiPM Fabricated at SCL, Mohali: Test results



[Ref] A. Yasser et.al, "Fabrication and Electrical Measurements of CMOS-integrated GM-APDs and Test Structures in 180nm CMOS Technology Platform," 2022 IEEE 19th India Council International Conference (INDICON), Kochi, India, 2022, pp. 1-4, doi: 10.1109/INDICON56171.2022.10040143.

SiPM Fabrication at Bharat Electronics Limited (BEL), Bangalore, India

BEL: working on the design and fabrication of SiPM on non-epitaxial structures

Targeted Technical Specification for Internal proactive development of SiPMs

Sl. No.	Parameter	Value
1	Number of Pixels	4 x4
2	Pixel Active area	3 mm x 3 mm
3	Number of microcells	4774
4	Size of microcell	35 micron x 35 micron
5	Typical Quench Resistor Value	200 kΩ to 300 kΩ
6	Typical Breakdown Voltage (VBR)	25 Volt
7	Typical Operating/Bias Voltage Range	(VBR + 1 Volt) to (VBR + 5 Volt)
8	Typical microcell Gain	3 x 10 ⁶ @ VBR+2.5 Volt @ RT
9	Device Light Sensitivity Range	300 nm to 800 nm, with peak sensitivity @ 400nm.
10	Rise time	~ 1 ns @ VBR + 2.5 Volt
11	Capacitance (anode to cathode)	850 pF @ VBR + 2.5







SiPM Fabrication at BEL, Bangalore, India: Mask Layout of SiPMs die



SiPM tests done @ NISER

SiPM was mounted on a PCB Connected in Reverse bias mode 10^{-4} Reverse bias voltage applied using Keithley 2470 10^{-4} sweep: 0 to 28 V (0.5 V step) \succ 10^{-5} 10^{-5} () 10⁻⁶ 10⁻⁷ 10^{-6} Current (A) -W 10^{-7} 8086994 10^{-8} SiPM 10^{-8} 10^{-} 3x3 mm² 23 24 25 26 27 Voltage (V) Si_detector1 10^{-9} HW 10^{-10} 15 0 5 10

I-V curve: Breakdown voltage ~26 V



SiPM tests done @ NISER

Tek Stop

After pulses

ise Time

Value

848mV

185.9ns

- SiPM was coupled to LYSO crystal
- Setup operated at 28 V reverse bias

Tektronix MDO3024 Mixed Domain Oscilloscope

200 MHz 2.5 GS/s

13 Feb 2023 06:24:11

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Max

792m

768m 171.8n

1.14 1.09 197.5

Std Dev

123m

116m

13 Feb 2023

06:25:03

Value

Peak-Peak

Rise Time

864m\

816m

178.7ns

952m

907m 183.0r

Single photo e- pulses and after-pulses are visible

Mean 1.04 991m 187.4n

800ns ∎→▼57,60000ns

Min

848m 800m 180.0n

1.256S/s 10k points

Std Dev

211m 211m

5,890

Max

1.38 1.32 195.4n

Available infrastructure and detector R&D: pad array development (ALICE FoCAL R&D)

FoCal-E R&D in India - past



Figure 2. Cross-section of the silicon pad sensor: three pads with the peripheral region (Distances are not to scale).



Figure 1. (left panel) Routing scheme in a single metal from individual pad to wire bond sites (Distances are not to scale), (right panel) Detailed corner view of the 6x6 silicon pad array.

6 cm x 6 cm



Design of 6x6 n-type detector developed by BEL, Bangalore

FoCal-E R&D in India - past



Figure 11. (A) Experimental setup at SPS-CERN. (B) 3-D plot showing the energy deposition in terms ADC count for different pads in a particular sensor layer (layer eight among the 19 layers) in response to the electron beam of 30 GeV incident energy. (C) The typical response of a pad in a particular sensor layer 120 GeV pion beam (MIP) [15]. (D) Response of pad 23 (array coordinate 2,3) of the sensor situated in the 8th layer for a wide range of incident energies of the incoming electron beam.

Ref: S. Mukhopadhyay et al "Development and characterization of a large area silicon pad array for an electromagnetic calorimeter", 2021 JINST 16 P09026

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NIM A 764 (2014) 24

JINST 15 (2020) 03, P03015

p-type single pad results



Radiation damage study was done at VECC-K130 cyclotron. The data are being analyzed. The dose, irradiate did not damaged the response in terms of I-V. Next experiment with higher dose is planned.

Ref.: Slide from Sanjib Muhuri, VECC

ALICE FoCal-E R&D in NISER – n-type



Ref.: All the Mask layout images are taken from slides of Indian Fab Engineer, BEL, Bangalore

25 n-type 8x9 pad array detector ready by March 2023

ALICE FoCal-E R&D in NISER – n-type

- Dummy wafer is 6" dia with all processes done
- Resistivity is 4 11 Ω .cm, thickness 675 μ m
- It will look exactly like a finished product wafer

Fabricated in Jan.2023 at BEL, Bangalore, India

8x9 n-type pad array fabricated on dummy wafer



ALICE FoCal-E R&D in NISER – n-type

Single pad array assembly with Front-end Electronics



- PCB fabrication and assembly order is given to one Indian company, Assembled PCB will be delivered by May 2023,
- PCB is designed by LPSC Grenoble, France for ALICE FoCal prototype
- NISER will get 25 HGCROC chips from the ALICE FoCal Collaboration

n-type pad – IV test setup

- Used Keithley 2470 source meter unit
- Simple python script sweeps the voltage and measure the leakage current and plots, copy data to file.



- - IV curve

n-type pad – test setup at NISER



HGCROCv2 - test setup

- Mainly prepared for performance testing of the packaged untested chips before gluing their carrier boards to the detector pad arrays, make sure the KCU105 board works (my motivation!)
- 25 single pad array PCB production is in progress
- Test results in the following slides are produced using a test framework developed by LPSC, Grenoble team



NISER Si group and background

- Team of 6 people: Interested in working on the EPIC-TOF project: two scientists (Ganesh Jagannath Tambave → Si hardware and Mriganka → physics simulations), one electronics engineer (Kirti Prasad Sharma), plus the support staff as mentioned on the last slide.
- . The group is currently part of the ALICE FOCAL project
 - Design, development, and production: n-and p-type pad array (8x9) on 6" wafer
 - Qualification studies of pad arrays (lab test, test beam experiments), ordered 25 pads
 - Focal physics simulations
- Dr. Tambave has a background in ALICE TPC upgrade (SAMPA ASIC tests) and ALICE ITS2 upgrade (ALPIDE MAPS tests, system integration), currently working on the ALICE FOCAL project
- 20 m² ISO-6 clean room, 40 m² workspace for silicon research lab, and various instruments required for detector qualification studies.
- Working on collective funding proposal for EIC EPIC, includes 18 national institutes in India



FoCAL Test beam at CERN, September 2022.

Simulation of THGEM detector @ NISER

- Field calculation was done by ANSYS and then the results were imported to Garfield++ for further calculations.
- The tool to simulate Electric Field configurations for the available THGEM setup is ready.
- The same tool can be used for simulating new designs.
- Very Preliminary efforts. The tools are getting ready. People are getting trained.



Thick GEM – First results @ NISER



GEM-based photo detector for PID @ BHU and IOP





Conversion of photons into photo-electrons High QE CsI/KBr/Diamond photocathode may be used. R & D simulation for Meta-materials for PID application, MPGD test facility

MPGD test setup at IoP Bhubaneswar





Detector R&D facilities @ NISER



Summary

- 18 National Indian institutes have expressed interest to participate in EIC EPIC project
- Nature of contribution is under discussion in early stage
- Working on collective research proposal wish to submit during this year
- Contribution on software front has already started and in good progress
- Hardware interests are in ZDC, RICH and ToF (Si detector R&D) in early stage
 - Experience with SiPM and Pad array fabrication, LGAD just started
- Experienced community exists in QCD physics experiments and we are open to any possible collaborations

Thank you!